

Title (en)

HALF-BRIDGE ELECTRONIC DEVICE COMPRISING TWO SYSTEMS FOR OPTIMISING DEAD-TIME BETWEEN THE SWITCHING OPERATIONS OF A HIGH LEVEL SWITCH AND OF A LOW LEVEL SWITCH

Title (de)

ELEKTRONISCHE HALBBRÜCKENVORRICHTUNG MIT ZWEI SYSTEMEN ZUR OPTIMIERUNG DER STILLSTANDSZEIT ZWISCHEN DEN SCHALTOOPERATIONEN EINES HOCHPEGELSCHALTERS UND EINES NIEDRIGPEGELSCHALTERS

Title (fr)

DISPOSITIF ELECTRONIQUE EN DEMI-PONT COMPRENANT DEUX SYSTEMES POUR L'OPTIMISATION DES TEMPS MORTS ENTRE LES COMMUTATIONS D'UN INTERRUPTEUR NIVEAU HAUT ET D'UN INTERRUPTEUR NIVEAU BAS

Publication

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Application

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Abstract (en)

[origin: WO2019224451A1] The invention relates to a half-bridge electronic device (100) comprising, in series, a low level switch (1) and a high level switch (2) connected at a central point (3), and respectively controlled by a first (SLS) and a second (SHS) activation/deactivation signal. The device (100) comprises:

- a first (10) and a second (20) synchronisation system configured to interpret a variation in the voltage (V_m) at the central point (3), respectively following a falling edge and following a rising edge, and to respectively generate a first (ATON-LS) and a second (ATON-HS) synchronisation signal separate from the first;
- a first (18) and a second (28) AND type logic gate respectively combining the first synchronisation signal (ATON-LS) with a first control signal (PWM-LS) and the second synchronisation signal (ATON-HS) with a second control signal (PWM-HS), in order to respectively form the first (SLS) and second (SHS) activation/deactivation signals.

IPC 8 full level

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CPC (source: EP US)

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